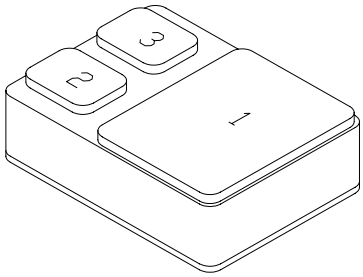
Solid State Devices, Inc.
14830 Valley View Blvd * La Mirada, Ca 90638
Phone: (562) 404-7855 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

SSR1510S.5

DESIGNER'S DATA SHEET

SMD.5



SSR1510

Screening [2/] __ = Commercial
TX = TX Level
TXV = TXV Level
S = S Level

Package: **S.5** = SMD.5

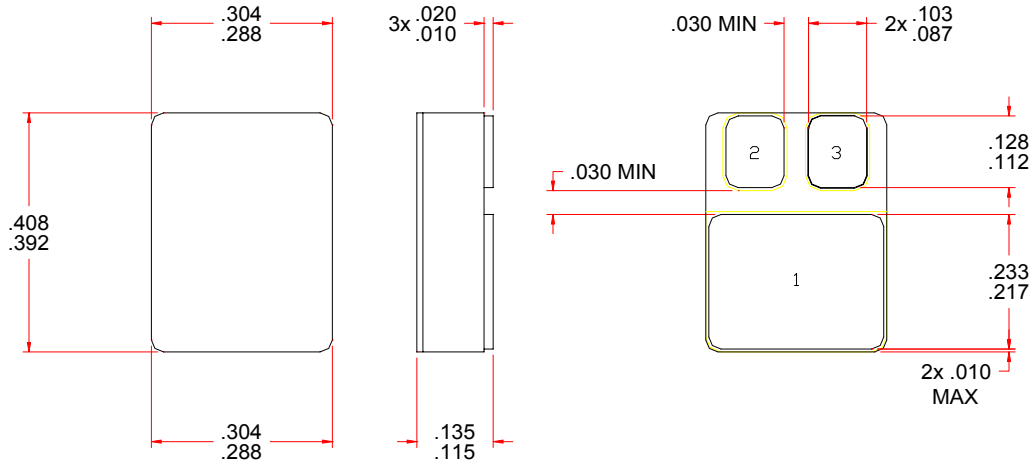
15 AMP /100 Volts
LOW VOLTAGE DROP
SCHOTTKY POWER DIODE

Features:

- Extremely Low Forward Voltage Drop
- Low reverse leakage
- Excellent high temperature performance
- Hermetically Sealed, low thermal resistance power Package
- Eutectic die attach and monometallic contacts for improved reliability
- Replacement for 15LJQ100 types
- TX, TXV, S-Level screening available

Maximum Ratings	Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current	I_O	15	A
Peak Surge Current 8.3 ms pulse, half sinewave superimposed on Io; allow junction to reach equilibrium in between pulses; Ta= 25ºC	I_{FSM}	250	A
Operating & Storage Temperature	T_{OP} & T_{STG}	-55 to +150	ºC
Maximum Thermal Resistance (Junction to Case)	$R_{\theta JC}$	2.25	ºC/W

PACKAGE OUTLINE:
SMD.5
PINOUT:
PIN 1: CATHODE
PIN 2: ANODE
PIN 3: ANODE



NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SH0034A DOC

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Electrical Characteristics [4/]		Symbol	Min	Typ	Max	Units
Instantaneous Forward Voltage Drop	I_F = 1 A	V_{F1}	—	460	—	mV
	I_F = 5 A	V_{F2}		600	635	
	I_F = 10 A	V_{F3}		710	—	
	I_F = 15 A	V_{F4}		850	890	
Instantaneous Forward Voltage Drop, Tc= 125 °C	I_F = 5 A	V_{F5}	—	500	520	mV
	I_F = 15 A	V_{F6}		675	700	
Instantaneous Forward Voltage Drop, Tc= -55 °C	I_F = 5 A	V_{F7}	—	625	—	mV
	I_F = 15 A	V_{F8}		825		
Reverse Leakage Current	V_R = 100V	I_{R1}	—	15	500	µA
Reverse Leakage Current, Tc= 75 °C	V_R = 100V	I_{R2}	—	500	—	µA
Reverse Leakage Current, Tc= 125 °C	V_R = 100V	I_{R3}	—	8	15	mA
Junction Capacitance	V_R = 5V, f= 1 MHz	C_{j1}	—	380	500	pF
	V_R = 10V, f= 1 MHz	C_{j2}	—	425	—	

NOTES:

* Pulse Test: Pulse Width = 300µsec, Duty Cycle = 2%.

4/ Unless Otherwise Specified, All Electrical Characteristics @25°C.